



# ACE7433M

## P-Channel 30-V MOSFET

### Description

The ACE7433M uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. This device is suitable for use as a high side switch in SMPS and general purpose applications.

### Features

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

### Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>a</sup>	$T_A=25^\circ\text{C}$	$I_D$	-20	A
	$T_A=70^\circ\text{C}$		-16	
Pulse Drain Current <sup>b</sup>		$I_{DM}$	-50	
Continuous Drain Current (Diode Continuous) <sup>a</sup>		$I_S$	-7.3	A
Power Dissipation <sup>a</sup>	$T_A=25^\circ\text{C}$	$P_D$	5	W
	$T_A=70^\circ\text{C}$		3.2	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$	25	$^\circ\text{C/W}$
	Steady State		65	$^\circ\text{C/W}$

#### Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

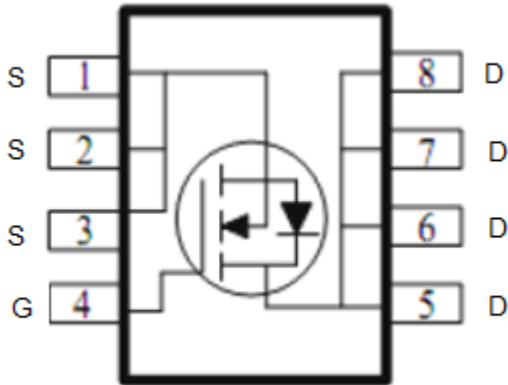


# ACE7433M

P-Channel 30-V MOSFET

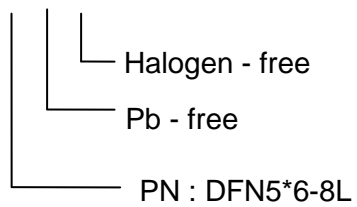
## Packaging Type

DFN5\*6-8L



## Ordering information

ACE7433M PN + H





# ACE7433M

## P-Channel 30-V MOSFET

### Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1			V
Gate Body Leakage	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$			-1	uA
		$V_{DS}=-24\text{V}, V_{GS}=0\text{V}, T_J=55^\circ\text{C}$			-25	
On-State Drain-Current <sup>a</sup>	$I_{D(on)}$	$V_{DS}=-5\text{V}, V_{GS}=-10\text{V}$	-30			A
Static Drain-Source On-Resistance <sup>a</sup>	$r_{DS(ON)}$	$V_{GS}=-10\text{V}, I_D=-15.3\text{A}$			9	m $\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-12.3\text{A}$			13	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{GS}=-15\text{V}, I_D=-15.3\text{A}$		34		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S=-3.7\text{A}, V_{GS}=0\text{V}$		-0.72		V
<b>Dynamic <sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15\text{V}, V_{GS}=-4.5\text{V}, I_D=-15.3\text{A}$		140		nC
Gate-Source Charge	$Q_{gs}$			35		
Gate-Drain Charge	$Q_{gd}$			62		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-15\text{V}, R_L=0.9\Omega, I_D=-15.3\text{A}, V_{GS}=-10\text{V}, R_{GEN}=6\Omega,$		18		ns
Rise Time	$t_f$			87		
Turn-Off Delay Time	$t_{d(off)}$			345		
Fall Time	$t_f$			226		
Input Capacitance	$C_{iss}$	$V_{DS}=-15\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		8500		pF
Output Capacitance	$C_{oss}$			1291		
Reverse Transfer Capacitance	$C_{rss}$			939		

Note:

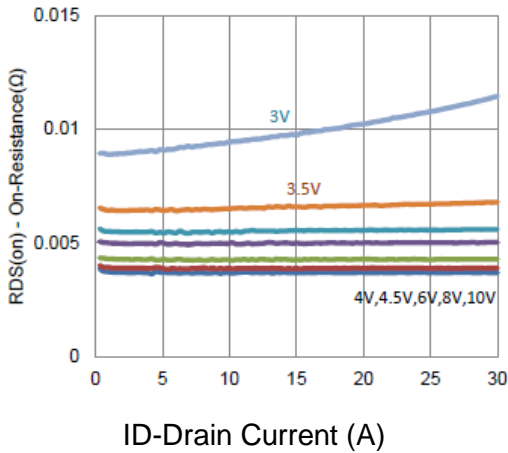
- a. Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.



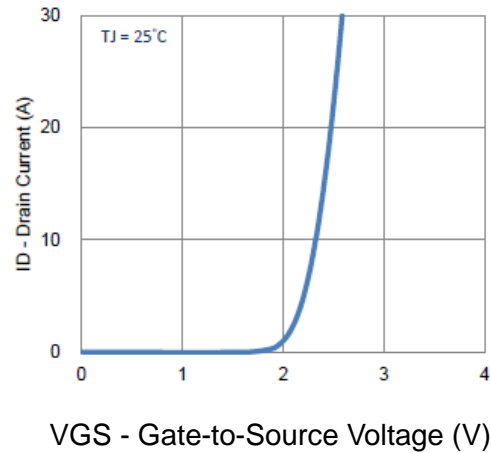
# ACE7433M

## P-Channel 30-V MOSFET

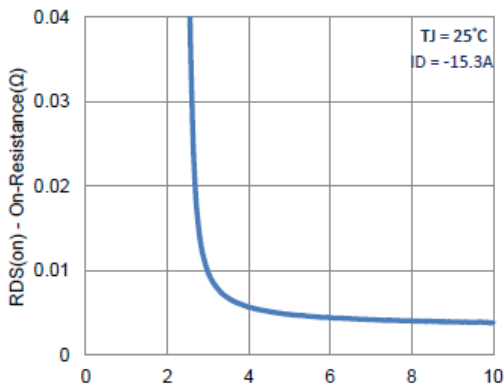
### Typical Performance Characteristics



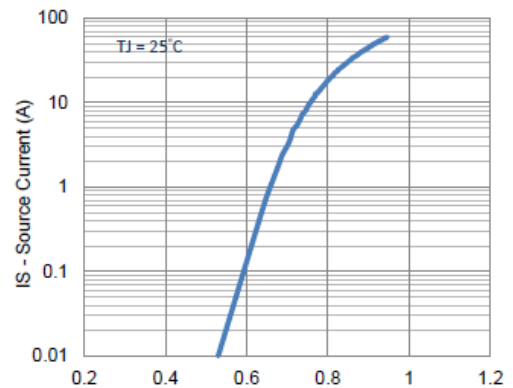
1. On-Resistance vs. Drain Current



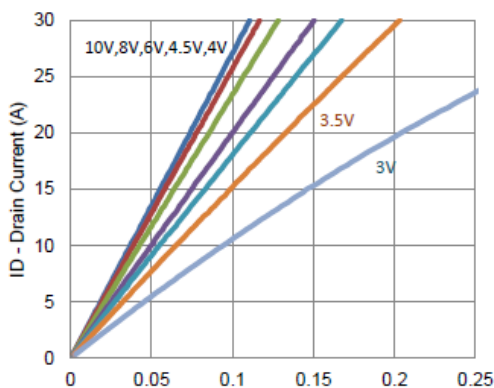
2. Transfer Characteristics



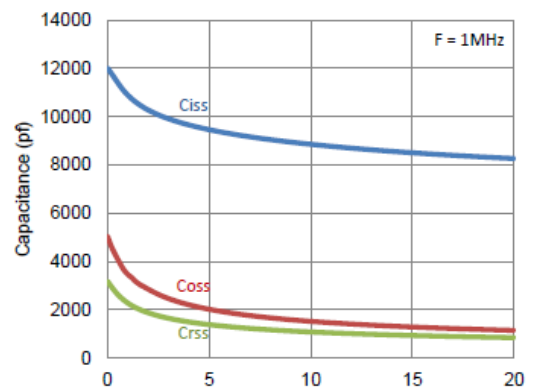
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics



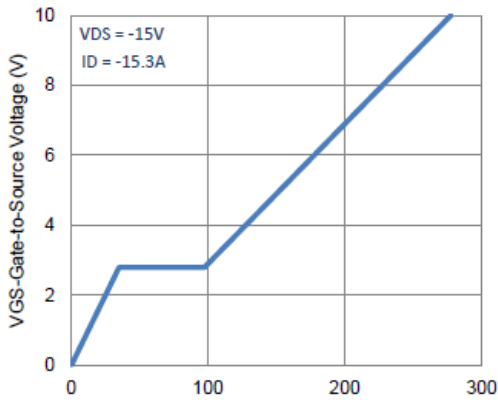
6. Capacitance



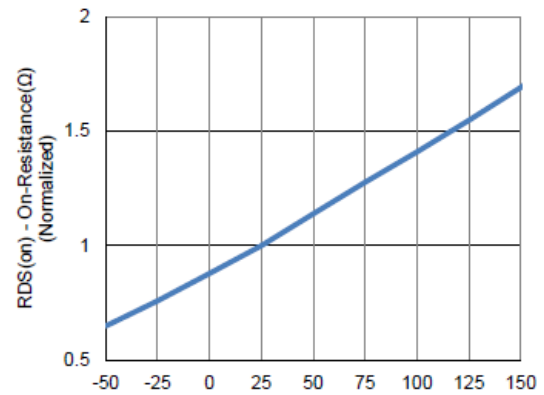
# ACE7433M

## P-Channel 30-V MOSFET

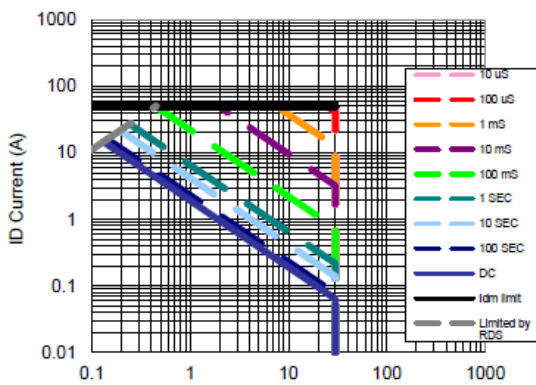
### Typical Performance Characteristics



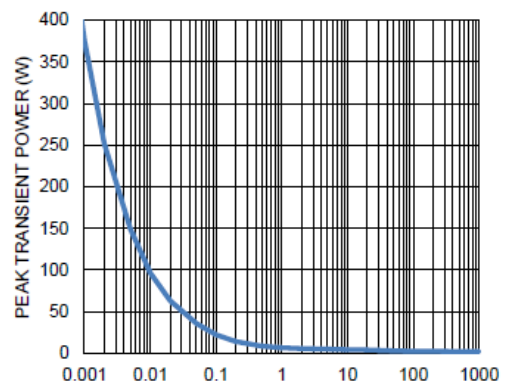
Qg - Total Gate Charge (nC)  
7. Gate Charge



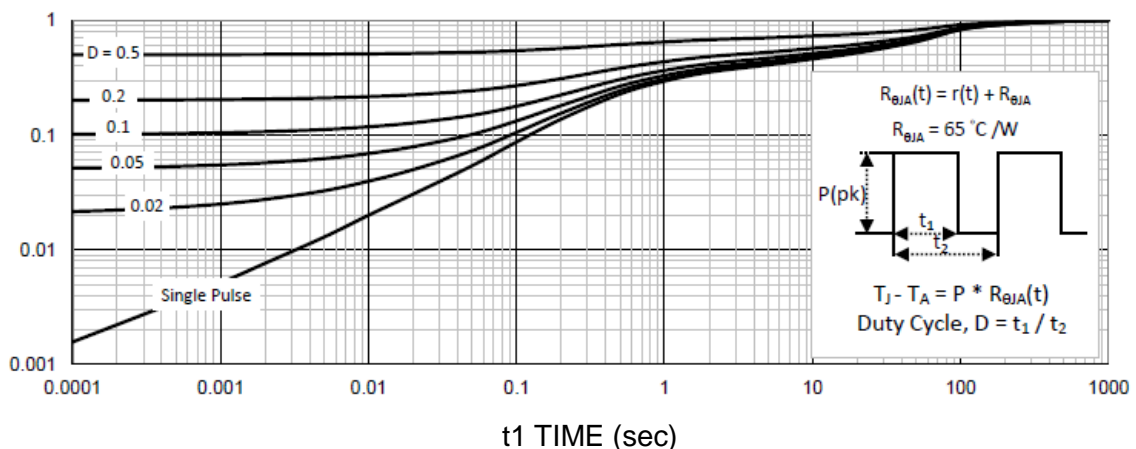
TJ - Junction Temperature (°C)  
8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)  
9. Safe Operating Area



t1 TIME (SEC)  
10. Single Pulse Maximum Power Dissipation



t1 TIME (sec)  
11. Normalized Thermal Transient Junction to Ambient

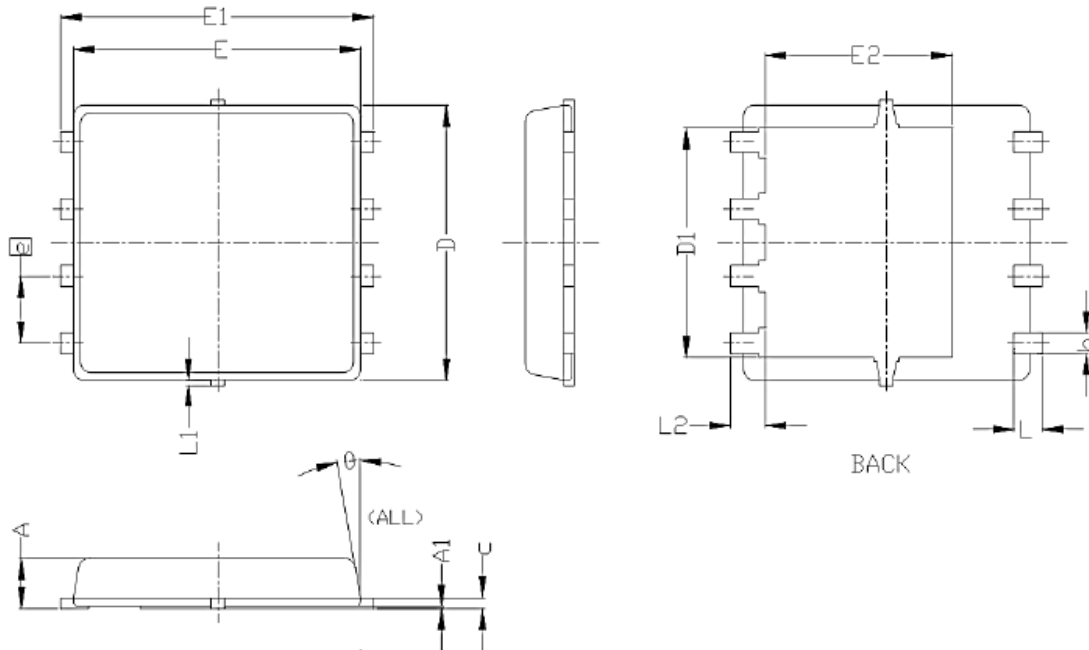


# ACE7433M

## P-Channel 30-V MOSFET

### Packing Information

#### DFN5\*6-8L



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.62 BSC			0.143 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0.15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°



# ACE7433M

## P-Channel 30-V MOSFET

### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ACE Technology Co., LTD.  
<http://www.ace-ele.com/>